

Abstract

A polycrystalline silicon material for producing silicon single crystal, containing a plurality of polycrystalline silicon chunks, in which assuming that a total concentration of donor elements present inside a bulk body of the polycrystalline silicon material is $Cd1$ [ppt], a total concentration of acceptor elements present inside the bulk body of the polycrystalline silicon material is $Ca1$ [ppt], a total concentration of the donor elements present on a surface of the polycrystalline silicon material is $Cd2$ [ppt], and a total concentration of the acceptor elements present on the surface of the polycrystalline silicon material is $Ca2$ [ppt], $Cd1$, $Ca1$, $Cd2$, and $Ca2$ satisfy a relation of $2 \text{ [ppt]} \leq (Cd1 + Cd2) - (Ca1 + Ca2) \leq 8 \text{ [ppt]}$.

[Figure 1]